HFZT

LJ2305

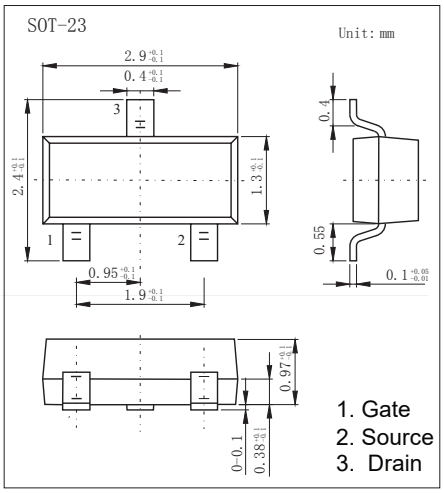
SOT-23 Plastic-Encapsulate MOSFETS

Features

- VDS (V) = -20V
- RDS(ON)＜0.052 Ω (VGS = -4.5V)
- RDS(ON)＜0.071 Ω (VGS = -2.5V)
- RDS(ON)＜0.108 Ω (VGS = -1.8V)
- P-Channel MOSFET

MECHANICAL DATA

- Case style:SOT-23molded plastic
- Mounting position:any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter		Symbol	Rating	Unit
Drain-source voltage Gate-source voltage		VDS VGS	-20 ±10	V V
Continuous drain current	TA=25℃ TA=70℃	ID	-3.5 -2.8	A
Pulsed drain current		IDM	-12	A
Power dissipation	TA=25℃ TA=70℃	PD	1.25 0.8	W
Thermal Resistance.Junction-to-Ambient		RθJA	130	℃/W
Operating junction and storage temperature range		Tj,Tstg	-55 to +150	℃

MOSFET ELECTRICAL CHARACTERISTICS Ta=25 ℃ unless otherwise specified

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Drain-source breakdown voltage	V_{DSS}	V_{GS} = 0 V, I_D = -250μA	-□			V
Gate threshold voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = -250 μA	-0.45		-0.8	V
Zero gate voltage drain current	I_{DSS}	V_{DS} = -20 V□ V_{GS} = 0 V			-1	μA
		V_{DS} = -20V□ V_{GS} = 0 V, T_J = 55 ℃			-10	
Gate-body leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} =□± 10 V			±100	nA
Drain-source on-state resistance	$r_{DS(on)}$	V_{GS} = -4.5 V, I_D = -3.5 A		0.044	0.052	Ω
		V_{GS} = -2.5 V, I_D = -3.0 A		0.060	0.071	
		V_{GS} = -2 V□, I_D = -2.0 A		0.087	0.108	
On-state drain current	$I_{D(on)}$	V_{DS}≤ -5 V, V_{GS} = -4.5 V	-6			A
		V_{DS}≤ -5 V, V_{GS} = -2.5 V	-3			
Forward transconductance	g_{fs}	V_{DS} = -5 V, I_D = -3.5 A		8.5		S
Input capacitance *	C_{iss}	V_{DS} = -10V ,V_{GS} = 0 , f = 1 MHz		1245		pF
Output capacitance *	C_{oss}			375		
Reverse transfer capacitance *	C_{rss}			210		
Total gate charge *	Q_g	V_{DS} = -10V ,V_{GS} = -4.5 V , I_D= -3.5 A		10	15	nC
Gate-source charge *	Q_{gs}			2		
Gate-drain charge *	Q_{gd}			2		
Turn-on Delay time	$t_{d(on)}$	V_{DD} = -5V , R_L = 4Ω , I_D = -1A , V_{GEN} =- 4.5V , R_G = 6Ω		13	20	ns
Turn-on Reise time	t_r			25	40	
Turn-off Dealy time	$t_{d(off)}$			55	80	
Turn-off Fall time	t_f			19	35	
Continuous source current (diode conduction) *	I_S			-1.6		A
Diode forward voltage	V_{SD}	I_S = -1.6 A, V_{GS} = 0 V			-1.2	V

* Pulse test: PW ≤ 300 μs duty cycle ≤ 2%.